



# **ISC Silicon NPN Power Transistor**

#### **DESCRIPTION**

- Continuous Collector Current-I<sub>C</sub>= 4A
- · Collector Power Dissipation-
  - : P<sub>C</sub>= 25W @T<sub>C</sub>= 25°C
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## **APPLICATIONS**



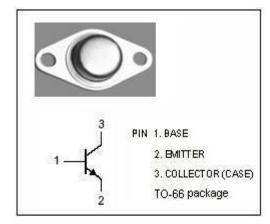
 Designed for general purpose switching and amplifier applications.

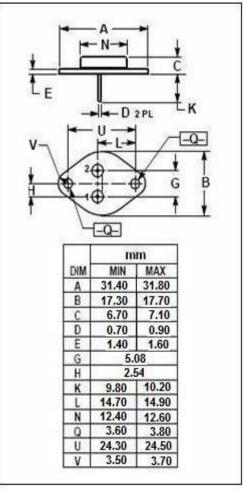
# ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

SYMBOL	MBOL PARAMETER		UNIT
V <sub>CBO</sub>	Collector-Base Voltage	90	V
$V_{CEX}$	Collector-Emitter Voltage V <sub>BE</sub> = -1.5V	90	V
V <sub>CEO</sub>	VCEO Collector-Emitter Voltage   VEBO Emitter-Base Voltage		V
V <sub>EBO</sub>			V
Ic	Collector Current-Continuous	4	А
I <sub>B</sub>	Base Current-Continuous	2	А
Pc	Collector Power Dissipation@Tc=25°C	25	W
TJ	Junction Temperature	200	$^{\circ}$
T <sub>stg</sub>	Storage Temperature	-65~200	$^{\circ}$

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT		
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	7.0	°C/W		







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BDY78

#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 30mA; I <sub>B</sub> = 0	55		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	90		V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 0.5A; I <sub>B</sub> = 50mA		1.0	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 1A		3.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 4V		2.0	V
I <sub>CEX</sub>	Collector Cutoff Current	V <sub>CE</sub> = 90V; V <sub>BE</sub> = -1.5V V <sub>CE</sub> = 90V; V <sub>BE</sub> = -1.5V, T <sub>C</sub> =150°C		1.0 5.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0		1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 4V	25	100	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 4V	5		
fτ	Current Gain-Bandwidth Product	I <sub>C</sub> = 0.2A; V <sub>CE</sub> = 10V	8		MHz

## **NOTICE:**

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